

L Number	Hits	Search Text	DB	Time stamp
2	44	resin near10 (polish\$4 or grind\$) near10 thick\$ same (back or back\$1side or rear) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/19 11:26
5	133	(resin near10 (polish\$4 or grind\$) near10 (back or back\$1side or rear) and semiconductor) not (resin near10 (polish\$4 or grind\$) near10 thick\$ same (back or back\$1side or rear) and semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/19 10:41
6	7	resin near10 (polish\$4 or grind\$) near10 thick\$ same bottom and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/19 11:28
7	54	resin near10 (polish\$4 or grind\$) near10 bottom and semiconductor not (resin near10 (polish\$4 or grind\$) near10 thick\$ same bottom and semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/19 11:49
31	150	etch\$ near10 (grind\$ or polish\$) near10 resin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/19 13:03
32	94	etch\$ near10 (grind\$ or polish\$) near10 resin and @py<2002	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/19 13:05
33	38	(etch\$ near10 (grind\$ or polish\$) near10 resin and @py<2002) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/19 13:06
-	120	resin near10 (back or back\$1sid\$) near10 (polish\$ or grind\$) and semiconduct\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/17 13:33
-	68	semiconductor near3 chip and resin same electrode same (polish\$ or grind\$) same (rear or back)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/17 14:30
-	30	semiconductor near3 chip same resin same electrode same (polish\$ or grind\$) same (rear or back)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/17 15:20
-	10	semiconductor near3 chip near10 active same resin same (polish\$ or grind\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/17 15:57
-	24	(sekine.in. adj kenji) and chip same substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/17 15:57
-	50	resin near10 (polish\$ or grind\$) near10 (rear or back or back\$1side) same electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/18 16:56

-	70	resin near10 (polish\$ or grind\$) near10 (rear or back or back\$1side) same chip	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/18 17:28
-	5	ichikawa.in. near2 kimiya and resin same semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/18 17:22
-	46	resin near10 (polish\$ or grind\$) near10 (rear or back or back\$1side) near20 expos\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/18 17:53
-	131	resin near10 (polish\$ or grind\$) near10 (rear or back or back\$1side) and chip	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/18 18:12
-	34	(resin near10 (polish\$ or grind\$) near10 (rear or back or back\$1side) and chip) not ((resin near10 (polish\$ or grind\$) near10 (rear or back or back\$1side) same electrode) or (resin near10 (polish\$ or grind\$) near10 (rear or back or back\$1side) same chip) or (resin near10 (polish\$ or grind\$) near10 (rear or back or back\$1side) near20 expos\$))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/19 10:17